

این دیتاشیت توسط توکل الکترونیک تهیه و ارائه شده است.
جهت مشاهده قیمت، موجودی و ثبت سفارش این قطعه به وبسایت توکل الکترونیک مراجعه فرمایید.



مشاهده قیمت و خرید

برای خرید و مشاهده سایر محصولات کلیک کنید



2N7012, 2N7013

N-Channel Enhancement Mode Transistors

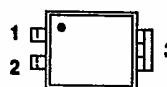
T-39-05

4-PIN DIP
(Similar to TO-250)

TOP VIEW

PRODUCT SUMMARY

PART NUMBER	$V_{(BR)DSS}$ (V)	$r_{DS(ON)}$ (Ω)	I_D (A)
2N7012	60	0.35	1.2
2N7013	40	0.35	1.2

1 GATE
2 SOURCE
3 DRAINABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS		UNITS
			2N7012	2N7013	
Drain-Source Voltage		V_{DS}	60	40	V
Gate-Source Voltage		V_{GS}	± 20	± 20	
Continuous Drain Current	$T_A = 25^{\circ}\text{C}$	I_D	1.2	1.2	A
	$T_A = 100^{\circ}\text{C}$		0.80	0.80	
Pulsed Drain Current ¹		I_{DM}	10	10	
Power Dissipation	$T_A = 25^{\circ}\text{C}$	P_D	1.0	1.0	W
	$T_A = 100^{\circ}\text{C}$		0.4	0.4	
Operating Junction & Storage Temperature Range		T_J, T_{stg}	-55 to 150		$^{\circ}\text{C}$
Lead Temperature ($1/16$ " from case for 10 sec.)		T_L	300		

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THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient	$R_{\theta JA}$		120	K/W

¹Pulse width limited by maximum junction temperature.

2N7012, 2N7013



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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	TYP	LIMITS		UNIT	
				MIN	MAX		
STATIC							
Drain-Source Breakdown Voltage	2N7012 2N7013	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	60 40		V	
Gate Threshold Voltage		$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 1000\text{ }\mu\text{A}$	2.0	4.0		
Gate-Body Leakage		I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$		± 100	nA	
Zero Gate Voltage Drain Current		I_{DSS}	$V_{DS} = V_{(BR)DSS}, V_{GS} = 0\text{ V}$		250	μA	
			$V_{DS} = 0.8 \times V_{(BR)DSS}, V_{GS} = 0\text{ V}, T_J = 125^\circ\text{C}$		1000		
On-State Drain Current ¹		$I_{D(ON)}$	$V_{DS} = 2\text{ V}, V_{GS} = 10\text{ V}$	1.2		A	
Drain-Source On-State Resistance ¹		$r_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 1.0\text{ A}$	0.3	0.35	Ω	
			$V_{GS} = 10\text{ V}, I_D = 1.0\text{ A}, T_J = 125^\circ\text{C}$	0.55	0.64		
Forward Transconductance ¹		g_{fs}	$V_{DS} = 15\text{ V}, I_D = 1.0\text{ A}$	1.5	1.2	S	
DYNAMIC							
Input Capacitance		C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	220		300	pF
Output Capacitance		C_{oss}		120		200	
Reverse Transfer Capacitance		C_{rss}		30		100	
Total Gate Charge ²		Q_g	$V_{DS} = 0.8 \times V_{(BR)DSS}, V_{GS} = 10\text{ V}, I_D = 15\text{ A}$	4.8		6.0	nC
Gate-Source Charge ²		Q_{gs}		1			
Gate-Drain Charge ²		Q_{gd}		2			
Turn-On Delay Time ²		$t_{d(on)}$	$V_{DD} = 30\text{ V}, R_L = 25\text{ }\Omega$ $I_D \simeq 1.2\text{ A}, V_{GEN} = 10\text{ V}, R_G = 25\text{ }\Omega$	7		20	ns
Rise Time ²		t_r		13		30	
Turn-Off Delay Time ²		$t_{d(off)}$		18		30	
Fall Time ²		t_f		13		25	
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_A = 25^\circ\text{C}$)							
Continuous Current		I_S			1.2	A	
Pulsed Current ³		I_{SM}			10		
Forward Voltage ¹		V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$		1.6	V	
Reverse Recovery Time		t_{rr}	$I_F = I_S, dI_F/dt = 100\text{ A}/\mu\text{s}$	45		ns	
Reverse Recovery Charge		Q_{rr}		0.6		μC	

¹Pulse test: Pulse Width $\leq 300\text{ }\mu\text{sec}$, Duty Cycle $\leq 2\%$.

²Independent of operating temperature.

³Pulse width limited by maximum junction temperature.

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Figure 1. Output Characteristics

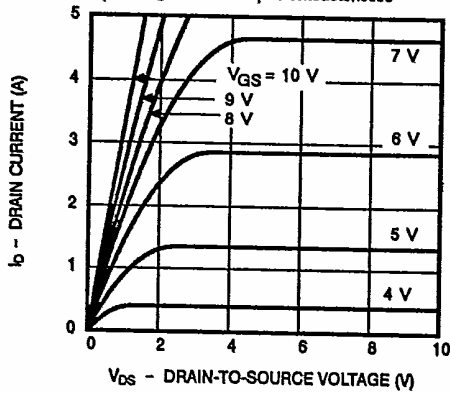


Figure 2. Transfer Characteristics

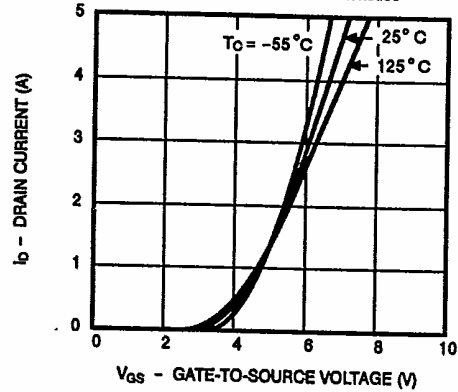


Figure 3. Transconductance

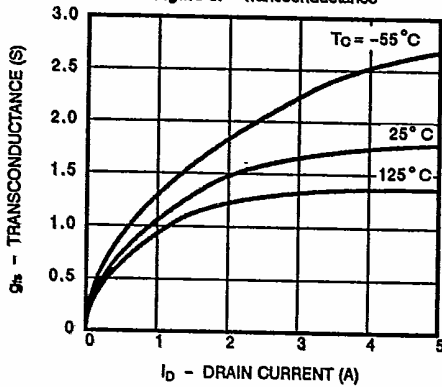


Figure 4. On-Resistance

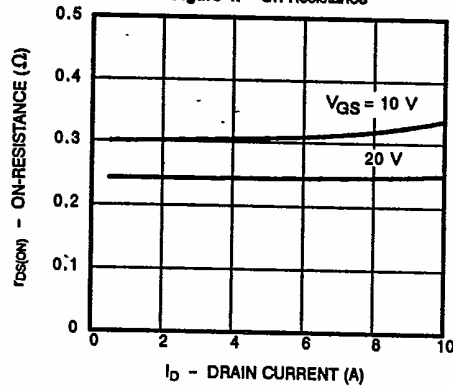


Figure 5. Capacitance

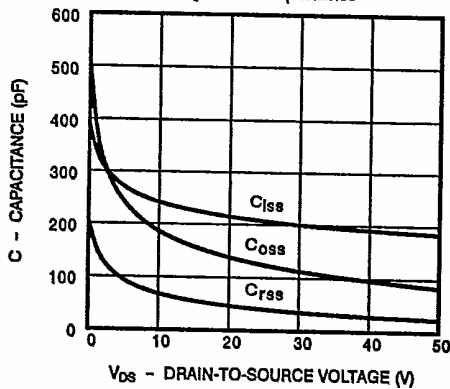
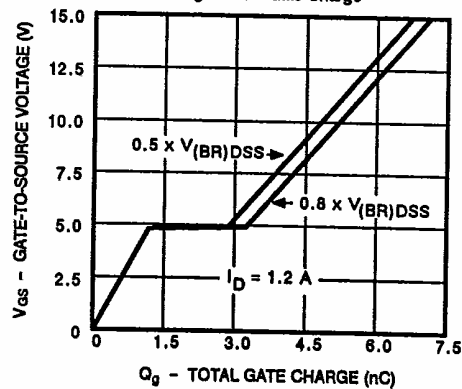


Figure 6. Gate Charge



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TYPICAL CHARACTERISTICS (Cont'd)

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Figure 7. On-Resistance vs. Junction Temperature

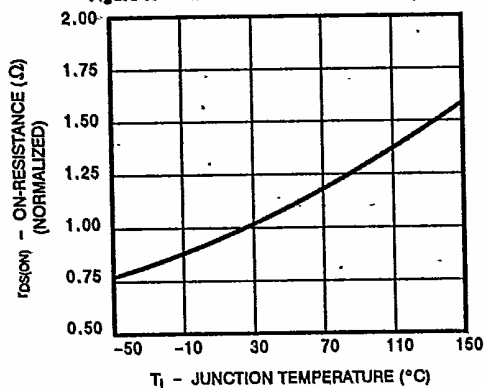
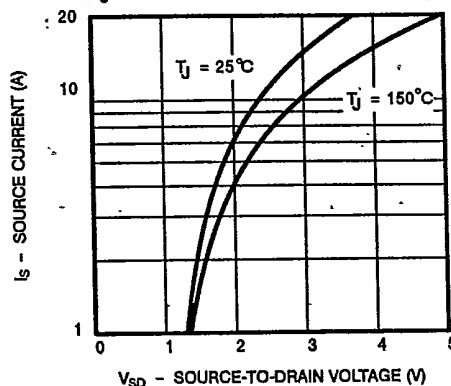


Figure 8. Source-Drain Diode Forward Voltage



THERMAL RATINGS

Figure 9. Maximum Drain Current vs. Ambient Temperature

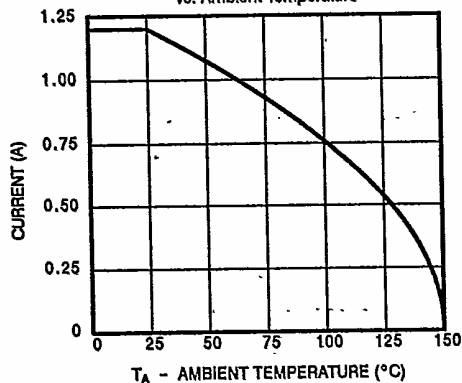


Figure 10. Safe Operating Area

